

Crystal vibration limit of nanoscale dynamic etalon. Rough estimate

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The paper analyzes the limits of nanoscale dynamic etalon caused by thermal vibration of crystalline structure. It is shown that exactly sufficiently long one-dimensional defect of crystal lattice should confine the standard accuracy within angstroms.

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One of the novel techniques of measuring objects of nanometer and subnanometer scales is related to creating dynamic etalons based on the precise measurements the tunnel microscope probe movements [1]. A linear dimension is transmitted from the etalon to a measuring system by means of a controlled movement of the etalon surface at a required distance and measurement of the above movement. In this case the real accuracy attained by the measuring system is limited by unpredictable vibrations of the crystal surface. The present paper is devoted to analysis of the fundamental limits of such system caused by thermal vibrations of crystal lattice.

The thermal deviation of crystal atoms from the equilibrium states is analyzed within the adiabatic approximation assuming the electron polarization to follow the relatively slow motion of atoms without delay. For molecular or covalent crystals like diamond, Ge, Si, GaAs the electron polarization effect is ignorable, whereas for ionic crystals (NaCl, CsCl, ZnS, etc.) this assumption is well justified for all the wave vectors of phonons except for a sufficiently small wave vectors $k_p \sim \Omega\sqrt{\epsilon}/c$ (see, e.g. Ref. [2, 3]). Here Ω is a characteristic frequency of optical phonons, ϵ is a crystal permittivity, and c is the light speed. In particular, for ZnS, where $\Omega \sim 6 \times 10^{13} \text{ s}^{-1}$ and $\epsilon \sim 7$, we get $k_p \sim 5 \times 10^3 \text{ cm}^{-1}$. By contrast, according to the results to be obtained, actually phonons with wave vectors about $k \lesssim 1/a \sim 2 \times 10^7 \text{ cm}^{-1}$ (a is a characteristic lattice spacing) mainly contribute to the characteristic values of atom thermal fluctuations.

To estimate possible effects caused by the crystal surface states and its defects we analyze 1D-, 2D- and 3D-models. It should be noted that in the cases of 1D- and 2D-models the corresponding lattice is assumed to be embedded in the 3D-space, so its atoms actually perform 3D-motion.

Let the lattice unit cell contain σ atoms and the value $\mathbf{r}_{\mathbf{n}\alpha}$ specify the displacement of atom α ($\alpha = 1, 2, \dots, \sigma$) in unit cell $\mathbf{n} = \{n_1, n_2, n_3\}$ ($n_i \in \mathbb{Z}$) from its equilibrium position $\mathbf{R}_{\mathbf{n}} = n_1\mathbf{a}_1 + n_2\mathbf{a}_2 + n_3\mathbf{a}_3$, where $\{\mathbf{a}_i\}$ are the crystalline spacing vectors (for the 2D-lattice $n_3 = 0$ and for the atom chain $n_2 = 0$ also). Then the corresponding operator $\hat{r}_{\mathbf{n}\alpha}$ and the conjugate creation-annihilation operators $b_{\mathbf{k}s}^+$, $b_{\mathbf{k}s}$ of phonons are related by the expression

(see, e.g., Ref. [2])

$$\hat{r}_{\mathbf{n}\alpha} = \sqrt{\frac{\hbar}{2Nm_\alpha}} \sum_{\mathbf{k},s} \frac{\mathbf{u}_{\alpha s}(\mathbf{k})}{\sqrt{\Omega_s(\mathbf{k})}} (b_{\mathbf{k}s} + b_{-\mathbf{k}s}^+) e^{i\mathbf{k}\mathbf{R}_{\mathbf{n}}}. \quad (1)$$

Here N is the total number of unit cells, the sum runs over all the possible wave vectors $\{\mathbf{k} \neq 0\}$ and all the modes, $s = 1, 2, \dots, 3\sigma$, describing different vibrations of atoms within one unit cell, m_α is the mass of atom α , $\Omega_s(\mathbf{k})$ is the frequency of the vibration type labeled by the pair $\{\mathbf{k}, s\}$. The eigenvectors $\mathbf{u}_{\alpha s}(\mathbf{k}) = \{u_{\alpha s}^{(l)}(\mathbf{k})\}$ ($l = 1, 2, 3$) of the corresponding vibration types meet the equalities

$$\sum_{\alpha=1}^{\sigma} \mathbf{u}_{\alpha s}(\mathbf{k}) \cdot \mathbf{u}_{\alpha s'}(\mathbf{k}) = \delta_{s,s'}, \quad (2)$$

where $\delta_{s,s'}$ is the Kronecker symbol. Besides, the phonon frequency meets the equality $\Omega_s(-\mathbf{k}) = \Omega_s(\mathbf{k})$, as well as the eigenvectors do, $\mathbf{u}_{\alpha s}(-\mathbf{k}) = \mathbf{u}_{\alpha s}(\mathbf{k})$.

In order to estimate the characteristic amplitude δh of atom thermal fluctuations near the equilibrium states let us calculate the value

$$\langle (\delta h)^2 \rangle \sim \frac{1}{3\sigma} \left\langle \sum_{\alpha} (\hat{r}_{\mathbf{n}\alpha})^2 \right\rangle \quad (3)$$

averaged over all the possible states of the equilibrium phonon ensemble with the temperature T and Hamiltonian

$$\hat{H} = \sum_{\mathbf{k},s} \Omega_s(\mathbf{k}) [b_{\mathbf{k}s}^+ b_{\mathbf{k}s} + \frac{1}{2}]. \quad (4)$$

In this way we get

$$\langle (\delta h)^2 \rangle \sim \frac{\hbar}{3N\sigma} \sum_{\mathbf{k},s} \frac{[n_s(\mathbf{k}) + \frac{1}{2}]}{M_s(\mathbf{k})\Omega_s(\mathbf{k})}, \quad (5)$$

where the occupation number of phonons in the state $|\mathbf{k}, s\rangle$ under the thermodynamic equilibrium with temperature T (measured in energy units) is

$$n_s(\mathbf{k}) = \left[\exp\left(\frac{\hbar\Omega_s(\mathbf{k})}{T}\right) - 1 \right]^{-1} \quad (6)$$

and $M_s(\mathbf{k})$ is some effective mean mass of atoms in the unit cell depending on the vibration mode that obeys the equality

$$\frac{1}{M_s(\mathbf{k})} = \sum_{\alpha} \frac{1}{m_{\alpha}} [\mathbf{u}_{\alpha s}(\mathbf{k})]^2. \quad (7)$$

Due to equality (2) the value $M_s(\mathbf{k})$ belongs to the interval $M_s(\mathbf{k}) \in [m_{\min}, m_{\max}]$, the boundary of the given interval are specified by the minimal and maximal masses of the unit cell atoms.

In estimating the value of $\langle (\delta h)^2 \rangle$ let us ignore the dependence of effective mass $M_s(\mathbf{k})$ on the wave vector $\mathbf{k}$, i.e. set it equal to some constant, $M_s(\mathbf{k}) = M_{\text{eff}}$. Within the adopted approximation sum (5) is reduced to the integral over the possible values of the phonon energy $E = \hbar\Omega$:

$$\sum_{\mathbf{k}, s} (\dots) \Rightarrow 3N\sigma \int_0^{E_{\max}} dE \rho(E) (\dots). \quad (8)$$

Here the density of the phonon states $\rho(E)$ describes their distribution over the interval from zero to some maximal value $E_{\max}$ and is to be normalized to unity,

$$\int_0^{E_{\max}} dE \rho(E) = 1, \quad (9)$$

because the total number of states $|\mathbf{k}, s\rangle$ must be equal to $3N\sigma$. Thereby estimate (5) can be represented as

$$\begin{aligned} \left\langle \frac{(\delta h)^2}{a^2} \right\rangle &\sim \frac{\hbar^2}{M_{\text{eff}} a^2} \int_0^{E_{\max}} dE \rho(E) \\ &\times \frac{1}{E} \left[\frac{1}{\exp\left(\frac{E}{T}\right) - 1} + \frac{1}{2} \right], \end{aligned} \quad (10)$$

where, as before, a denotes the characteristic value of the crystal lattice spacing.

The upper boundary of the phonon energies $E_{\max}$ can be estimated using the characteristic frequency of the optical phonons Ω_{opt} or what is the same the characteristic frequency of individual atom vibrations in crystal lattices, $E_{\max} \sim \hbar\Omega_{\text{opt}}$ (see, e.g., [2]). For example, dealing with ZnS we have $\Omega_{\text{opt}} \sim 6 \times 10^{13} \text{ s}^{-1}$, which corresponds to temperatures about $T_D \sim \hbar\Omega_{\text{opt}}/k_B \sim 460 \text{ K}$.

To be specific in what follows we confine our consideration to the case of not too high temperatures, $T \lesssim T_D$. Besides, setting $M_{\text{eff}} \sim 40$ atomic units (for ZnS atomic masses of the compounds are $M_{\text{Zn}} \approx 69$ and $M_{\text{S}} \approx 32$) and $a \sim 3 \text{ \AA}$ the following estimates of the cofactor in formula (10)

$$\Re := \frac{\hbar^2}{M_{\text{eff}} a^2} \cdot \frac{1}{\hbar\Omega_{\text{opt}}} \sim 3 \times 10^{-4} \quad (11)$$

is obtained. Therefore it is possible to ignore the effect of quantum fluctuations (the summand $1/2$ in expression (10)), so

$$\left\langle \frac{(\delta h)^2}{a^2} \right\rangle \sim \frac{\hbar^2}{M_{\text{eff}} a^2} \int_0^{E_{\max}} dE \frac{\rho(E)}{E [\exp\left(\frac{E}{T}\right) - 1]}. \quad (12)$$

If the phonon spectrum would be characterized by a single frequency Ω , i.e. $\rho(E) = \delta(E - \hbar\Omega)$, then the desired estimate has taken the form

$$\begin{aligned} \left\langle \frac{(\delta h)^2}{a^2} \right\rangle &\sim \frac{\hbar}{M_{\text{eff}} a^2 \Omega} \left[\exp\left(\frac{\hbar\Omega}{T}\right) - 1 \right]^{-1} \\ &\sim \frac{T}{M_{\text{eff}} a^2 \Omega^2} \quad \text{for } T \gtrsim \hbar\Omega. \end{aligned} \quad (13)$$

This expression actually corresponds to the model of a disconnected oscillator ensemble and the lower line of expression (13) matches the estimate of the amplitude of classical oscillator affected by the white noise with intensity T . For $T \sim \hbar\Omega$ and $\Omega \sim \Omega_{\text{opt}}$ the value of the given estimate is evaluated by expression (11). It is actually an estimate of the thermal vibration amplitude of a point defect in the bulk or surface of the crystal. So their effects on the accuracy of the nanoscale dynamical standard may be ignored.

In order to get a more realistic estimate we will make us of the Debay model approximating the real phonon spectrum with solely acoustic phonons where $\Omega_s(\mathbf{k}) \propto k$. It is equivalent to approximating the phonon density ρ as follows

$$\rho(E) = D \frac{E^{D-1}}{E_{\max}^D} \quad (14)$$

where D is the dimension of the crystal lattice under consideration, $D = 1, 2, 3$. Then, taking into account the adopted assumption about the value of temperature, $T \lesssim T_D$ (recall that $k_B T_D := E_{\max} := \hbar\Omega_D$), we can set the upper boundary of integral (12) to infinity and, thus, rewrite expression (12) as

$$\left\langle \frac{(\delta h)^2}{a^2} \right\rangle \sim D \Re \left(\frac{T}{T_D} \right)^{D-1} \int_0^{\infty} dx \frac{x^{D-1}}{x [\exp(x) - 1]}. \quad (15)$$

For the 3-dimensional lattice crystal integral (15) is reduced to the following

$$\left\langle \frac{(\delta h)^2}{a^2} \right\rangle \sim \frac{\pi^2 \Re}{2} \left(\frac{T}{T_D} \right)^2, \quad (16)$$

i.e. again thermal vibrations of solid bulk has a minor effect on the accuracy of dynamical nanostandard.

For the 2-dimensional (plane) lattice integral (15) has a formal logarithmic singularity that has to be cut off at small energies related to phonons with very long wavelengths bounded by the crystal size or surface structures. It leads to appearing some cofactor L_n in the expression

$$\left\langle \frac{(\delta h)^2}{a^2} \right\rangle \sim \Re L_n \left(\frac{T}{T_D} \right), \quad (17)$$

but its value cannot be too large, typically such effects are reduced to $L_n \sim 10$. So, again, possible phonon modes localized at crystal surface which have be simulated with

the 2-dimensional lattice, has an insignificant effect of the standard accuracy.

For the 1-dimensional chain the situation changes dramatically. Integral (15) has a singularity of the type $1/x$ and its long-wave vibrations give rise to significant deviation of atoms from the equilibrium positions, i.e.

$$\left\langle \frac{(\delta h)^2}{a^2} \right\rangle \sim \Re\left(\frac{T\ell}{\hbar c_s}\right), \quad (18)$$

because the lower boundary of the phonon energy can be estimated as $\hbar c_s/\ell$ where $c_s \sim 10^5$ cm/s is sound velocity in solids and ℓ is the length of the chain. Setting $k_B T \sim \hbar \Omega_D \sim \hbar c_s/a$ and $\ell \sim 1$ mm we get the conclu-

sion that the latter cofactor in expression (18) gets the order of 10^7 . In fact, the considered oscillator chain simulating one-dimensional defects of crystal lattice is rather formal. Real atoms forming such defects embedded in solid bulk cannot deviate from their equilibrium positions for distances exceeding the lattice spacing. So we could expect that exactly sufficiently long low-dimensional defects limit the accuracy of the dynamical nanostandard on scale about angstroms on the side of thermal solid vibrations.

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- [1] L.A. Maximov, V.N. Berezovskiy, P.N. Luskinovich, V.A. Zhabotinskiy, *Device for precision displacement*. Patent pending # 8470; 2004138236/28(041577).
 [2] A. S. Davydov, *Theory of solid state*, (Moscow: "Nauka"

- Publ. 1976) (in Russian)
 [3] J. M. Ziman, *Principles of the Theory of Solids* (Cambridge: Cambridge University Press, 1972).